



Group Art Unit: 2811

Examiner:

Docket No.:

S. Hu

110791

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Yasushi YAMAZAKI et al.

Application No.: 09/970,766

Filed: October 5, 2001

METHOD OF MANUFACTURING SEMICONDUCTOR SUBSTRATE, For:

SEMICONDUCTOR SUBSTRATE, ELECTRO-OPTICAL APPARATUS AND

ELECTRONIC EQUIPMENT

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

In reply to the July 31, 2002 Office Action, the period for response being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 20, line 14 – page 21, line 2, delete current paragraph and insert therefor:

By the above-mentioned processes, it is possible to manufacture the semiconductor substrate 7 having the single crystal semiconductor layer 1c in which the thicknesses are different depending on the portions. In this embodiment, the example is described in which one semiconductor substrate 7 is manufactured. In practice, however, the above-mentioned processes are done by using a large size of a manufacture support substrate through which a plurality of semiconductor substrates can be manufactured. Then, it is cut into individual semiconductor substrates after the semiconductor substrate is manufactured or after the semiconductor device is formed on the semiconductor substrate. The employment of such a